

L19	3504	18 and (divid\$3 singulat\$3 dic\$3 separat\$3 )	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:46
L20	400	19 not 8	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:46
L21	186	((((scribe near3 line) and dic\$3) and saw\$3) and (groove (break\$3 near5 point))	US-PGPU B; USPAT	OR	ON	2005/05/20 13:02
L22	12	((((scribe near3 line) and dic\$3) and saw\$3) and (groove (break\$3 near5 point))	USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/20 13:02

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	828315	(substrate wafer)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:43
L4	438313	3 and (trench groove recess open\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:43
L5	39536	4 and ((encapsulat\$3 encapsulant resin) same (recess groove trench open\$3))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:44
L6	8652	5 and (die dice)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:44
L7	4860	6 and wir\$3	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:45
L8	3505	7 and ((top upper) and (bottme lower))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:45
L9	3104	8 and (divid\$3 singulat\$3 dic\$3 separat\$3 )	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:46
L13	1378972	(substrate wafer)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/20 12:43
L14	162992	13 and (trench groove recess open\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/20 12:44
L15	9938	14 and ((encapsulat\$3 encapsulant resin) same (recess groove trench open\$3))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/20 12:44
L16	445	15 and (die dice)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/20 12:44
L17	121	16 and wir\$3	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/20 12:54
L18	3982	7 and ((top upper) and (Bottom lower))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/20 12:46